

U.S. Application No. 10/646,806

Docket No.: YOR920000543US2

**AMENDMENTS TO THE CLAIMS**

1-19. (Cancelled).

20. (Currently amended). A composite structure comprising:

a substrate having a major surface; and

a resist image having a feature size of less than about 0.2 microns formed on said major surface, wherein said resist image is formed by:

providing a layer of a resist on said major surface,

lithographically exposing said resist,

immersing said exposed resist in a developing fluid thereby forming an image in said resist,

maintaining the upper surface of said image in contact with a fluid,

rinsing said resist image with a rinse fluid,

overcasting said image with a stabilizing film while said resist image remains immersed in a fluid,

displacing said fluid in contact with said overcast image with a low surface tension final displacing fluid, wherein said displacing fluid is a solvent for said film, and

removing said film and said displacing fluid by critical point drying.

21. (Previously presented). The composite structure, according to claim 20, wherein a replicate pattern of said resist image is transferred into said major surface.

22. (Previously presented). The composite structure, according to claim 21, wherein pattern transfer comprises etching.

23. (Previously presented). The composite structure, according to claim 21, wherein pattern transfer comprises ion implantation.

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24. (Previously presented). The composite structure, according to claim 21, wherein said substrate is a semiconductor substrate.

25. (Previously presented). A semiconductor device fabricated using the resist-semiconductor composite structure, according to claim 20.